

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	99	(work function) with ((WSi) or (tungsten silicide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/10 14:29
L3	24	(work function) with ((WSi) or (tungsten silicide)) with (content or amount or ratio or concentration)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/10 17:58
S2	25	"6130145"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/26 19:32
S3	47	"5913145"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/26 19:50
S4	45047	(substrate or wafer) and (oxide or (gate insulat\$3)) and ((Tungsten nitride) or (tungsten carbide) or (tungsten silicide) or WSi or WN or WC)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:00
S5	1240	((Tungsten nitride) or (tungsten carbide) or (tungsten silicide) or WSi or WN or WC) with (onto or on or over or above) with (oxide or (gate insulat\$3))) and S4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:02
S6	252	((poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si)) with (onto or on or above or over) with ((Tungsten nitride) or (tungsten 1carbide) or (tungsten silicide) or WSi or WN or WC)) and S5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:03

S8	8	((poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si)) adj3 (onto or on or above or over) adj3 ((Tungsten nitride) or (tungsten 1carbide) or (tungsten silicide) or WSi or WN or WC)) and S5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:33
S9	0	((poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si)) adj2 (onto or on or above or over) adj2 ((Tungsten nitride) or (tungsten 1carbide) or (tungsten silicide) or WSi or WN or WC))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:39
S10	9	((poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si)) adj3 (onto or on or above or over) adj3 ((Tungsten nitride) or (tungsten 1carbide) or (tungsten silicide) or WSi or WN or WC))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:39
S11	47021	((tungsten carbid) or WC)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:48
S12	6090	(substrate or wafer) and (oxide or (gate insulat\$3)) and S11	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:49
S13	3	"W(CO)" and S12	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:49
S15	7	((tungsten carbid) or WC) with (onto or over or above or on) with (poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 12:53

S16	287943	(precursor or carrier) with (carbon or C)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:38
S17	16416	((precursor or carrier) with (Silicon or Si)) and ((precursor or carrier) with (carbon or C)) and ((precursor or carrier) with (nitrogen or N))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:41
S18	1113	(substrate or wafer) and ((gate oxide) or (gate insulat\$3)) and S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:41
S19	835219	(precursor or carrier or source) with (metal or Tungsten or titanium or tantallum or cobalt or Co or W or Ti or Ta or Mo or Re or Ru or Ni or nickle or ruthenium or molybdenum)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:45
S20	916	S18 and S19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:45
S21	130	(ethylene or allyl alcohol or (formic acid) or (tetrahydrofuran)) and S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:48
S22	76945	(precursor or carrier) with (carbon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:57
S23	1308	(substrate or wafer) and ((gate oxide) or (gate insulat\$3)) and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:57

S24	997	S19 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:58
S25	194	(ethylene or (allyl alcohol) or (formic acid) or (tetrahydrofuran)) and S24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 17:58
S26	20	("6218711" "6352872" "6395589" "6406951" "6492694" "6537369" "6603156" "6624483" "6727550").PN. OR ("6909186").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 18:53
S27	35	((WN) or (tungsten nitride)) same (dop\$3 or impalnt\$5) same carbon same gate	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 19:25
S28	8	((WCN) or (tungsten carbon nitride)) same barrier same gate	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 19:48
S29	196	((WCN) or (tungsten carbon nitride)) same barrier	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 19:55
S30	5	((tungsten silicide) or WSi) and (poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si)) and S29	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 19:56
S31	7	((metal Silicide) or ((titanium or tantalum or ruthenium or nickle or molybdenum or Cobalt or W or Ta or Ti or Co or Ni or Re or Ru or Mo) silicide)) and (poly or (poly Si) or (poly silicon) or (polycrystalline silicon) or (polycrystalline Si)) and S29	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 20:02
S32	115	(metal carbon nitride) or ((titanium or tantalum or ruthenium or nickle or molybdenum or Cobalt or W or Ta or Ti or Co or Ni or Re or Ru or Mo) ((carbon nitride) or (CN))) same barrier and gate	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/27 20:04

S35	2	JP "2003273350"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 21:01
S36	3	"20050110098"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 21:02
S37	127	(work function) with control \$4 with (CONTENT OR AMOUNT OR RATIO OR CONCENTRATION) WITH (N or Si or nitrogen or silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 21:12
S38	133	"6027961"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 21:28
S41	2	jp "10303412"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/27 21:50
S43	267	(ammonia or "NH.sub.3") and (W(CO)".sub.6") and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/28 06:31
S44	2	"20010014521"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/28 07:17
S45	80	"5654237" "5470791" "5304510" "5192714"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/05/28 08:39
S46	19	carbon and S45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/05/28 08:40

S47	2281	(257/288).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:11
S48	278	(257/388).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:11
S49	341	(257/407).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:11
S50	1246	(257/412).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:11
S51	563	(257/413).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:11
S52	634	(257/e29.16).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:13
S53	305	(257/e29.161).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:13
S54	506	(257/e21.621).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:13
S55	274	(257/e21.622).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:14
S56	335	(257/e21.623).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:14
S57	526	(257/e21.635).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:14
S58	720	(257/e21.636).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:14
S59	1563	(257/e21.637).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/28 09:14

EAST Search History (I nterference)

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